

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Previously presented) A polycrystalline silicon substrate for use in a photoelectric conversion element, comprising a region which contains concentrations of impurities that satisfy the following relations:

$[O_i] \geq 2E17$  [atoms/cm<sup>3</sup>] (Condition 1a) and

$[C] \leq 1E17$  [atoms/cm<sup>3</sup>] (Condition 2)

where  $[O_i]$  is an interstitial oxygen concentration determined by Fourier transform infrared spectroscopy and  $[C]$  is a total carbon concentration determined by secondary ion mass spectrometry;

wherein the polycrystalline silicon substrate is doped with boron.

2. (Original) A polycrystalline silicon substrate according to claim 1, wherein the substrate is sliced out from an ingot.

3. (Original) A polycrystalline silicon substrate according to claim 2, wherein the substrate satisfies the Condition 1a and the Condition 2 at all regions excluding a 1 cm wide peripheral edge portion.

4. (Previously presented) A polycrystalline silicon substrate for use in a photoelectric conversion element, comprising a region which contains concentrations of impurities that satisfy the following relations:

$[O_i] + 30 \times [N] \geq 2E17$  [atoms/cm<sup>3</sup>] (Condition 1b) and

$[C] \leq 1E17$  [atoms/cm<sup>3</sup>] (Condition 2)

wherein  $[O_i]$  is an interstitial oxygen concentration determined by Fourier transform infrared spectroscopy,  $[N]$  is a total nitrogen concentration determined by

second ion mass spectrometry, and [C] is a total carbon concentration determined by secondary ion mass spectrometry;

wherein the polycrystalline silicon substrate is doped with boron.

5. (Original) A polycrystalline silicon substrate according to claim 4, wherein the substrate is sliced out from an ingot.

6. (Original) A polycrystalline silicon substrate according to claim 5, wherein the substrate satisfies the Condition 1b and the Condition 2 at all regions excluding a 1 cm wide peripheral edge portion.

7. (Previously presented) A polycrystalline silicon ingot for use in a photoelectric conversion element, comprising a region which contains concentrations of impurities that satisfy the following relations:

$[O_i] \geq 2E17$  [atoms/cm<sup>3</sup>] (Condition 1a) and

$[C] \leq E17$  [atoms/cm<sup>3</sup>] (Condition 2)

where  $[O_i]$  is an interstitial oxygen concentration determined by Fourier transform infrared spectroscopy and [C] is a total carbon concentration determined by secondary ion mass spectrometry;

wherein the polycrystalline silicon ingot is doped with boron.

8. (Previously presented) A polycrystalline silicon ingot for use in a photoelectric conversion element, comprising a region which contains concentrations of impurities that satisfy the following relations:

$[O_i] + 3 \times [N] \geq 2E17$  [atoms/cm<sup>3</sup>] (Condition 1b) and

$[C] \leq 1E17$  [atoms/cm<sup>3</sup>] (Condition 2)

where  $[O_i]$  is an interstitial oxygen concentration determined by Fourier transform infrared spectroscopy, [N] is a total nitrogen concentration determined by secondary ion mass spectrometry, and [C] is a total carbon concentration determined by secondary ion mass spectrometry;

wherein the polycrystalline silicon ingot is doped with boron.

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